Code: 13A04504



B.Tech III Year I Semester (R13) Regular Examinations December 2015

## **DIGITAL IC APPLICATIONS**

(Electronics and Communication Engineering)

Time: 3 hours Max. Marks: 70

### PART - A

(Compulsory Question)

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1 Answer the following:  $(10 \times 02 = 20 \text{ Marks})$ 

- (a) Draw the ideal characteristics of a CMOS inverter and compare it with the actual characteristics
- (b) What is noise margin? Find out the noise margin from the actual characteristics of the inverter
- (c) Draw the transition times for CMOS circuits with: (i) ideal case of zero-time switching. (ii) a more realistic approximation. (iii) Actual timing, showing rise and fall times.
- (d) What are the various steps in an HDL-based design flow?
- (e) What is a register? How many different types data can be entered and retrieved?
- (f) What is mean by Universal Register? Name any one commercial universal register.
- (g) Distinguish between Mealy and Moore machines with suitable diagrams.
- (h) A sequence detector produces a '1' for each occurrence of the input sequence '1001' at its input. Draw the state-transition diagram of the FSM realizing the sequence detector.
- (i) What is meant by PLD? What are the advantages of PLDs?
- (j) Explain positive and negative edge triggered Flip-Flops.

### PART - B

(Answer all five units,  $5 \times 10 = 50 \text{ Marks}$ )

UNIT – I

- 2 (a) Compare the characteristics of the different types of MOS inverters in terms of noise margin and power dissipation.
  - (b) Draw neat circuit diagram, function table and logic symbol of a 2- input CMOS NAND gate.

OR

- 3 (a) Explain the principle of a Emitter-Coupled Logic (ECL/CML) through Basic ECL inverter/buffer circuit with input HIGH and LOW.
  - (b) What are the advantages and disadvantages of ECL?

[ UNIT - II ]

- 4 (a) Draw the VHDL program file structure and explain the same with the syntax of a VHDL entity declaration and architecture definition.
  - (b) Write the syntax of a VHDL function definition and write a VHDL function for converting STD\_LOGIC\_VECTOR to INTEGER.

OR

- 5 (a) Write the syntax of a VHDL component declaration and by making use of component declaration write a VHDL program for a prime-number detector.
  - (b) Write the syntax of a VHDL process statement and by making use of process statements write a process-based dataflow VHDL architecture for the prime-number detector.

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# (UNIT – III

Draw the logic symbol, truth table, logic diagram of a commercially available MSI 74x138 3-to-8 6 binary decoder and model the same using data flow-style VHDL program.

Draw the logic symbol, truth table, logic diagram of a commercially available MSI 74x157 2-input, 7 4-bit multiplexer and model the same using behavioral-style VHDL program.

# UNIT - IV

Draw the logic symbol, arithmetic conditions, logic diagram of a commercially available MSI 8 74x682 8-bit comparator and model the same using VHDL program.

9 Describe the internal structure, functional operation and timing of edge-triggered commercially available SSI 74x74 D flip-flop and model the same using behavioral-style VHDL program with preset and clear.

# [ UNIT – V ]

- 10 Draw the logic diagram of a simple 8x4 diode ROM and explain its operation.
  - List out commercial ROM types and compare them with respect to technology, read cycle, write cycle and comment on each one.
  - (c) How the limitations of a ROM-based realization are overcome in a PLA based realization?

### OR

- (a) Sketch the basic structure of a 2<sup>n</sup> x b RAM and functional behavior of a SRAM cell. 11
  - (b) Explain how read and write operations are performed in a SRAM with the help of timing diagrams.
  - .ac. Expl. (c) In what way the DRAMs differ from SRAMs? Explain the read and write operations for one transistor DRAM cell.

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